

P-Channel 100-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (mΩ) (Typ.)	I _D (A)	Q _g (Typ.)
- 100	185 at V _{GS} = - 10 V	- 3.8	7.9 nC
	212 at V _{GS} = - 4.5 V	- 3.0	

FEATURES

- DT-Trench Power MOSFET
- 100 % Rg and UIS tested
- Ultra Low On-Resistance

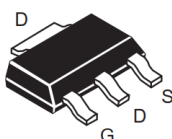


RoHS
COMPLIANT

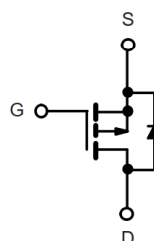
APPLICATIONS

- Active Clamp Circuits in DC/DC Power Supplies

SOT-223



Top View



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted				
Parameter	Symbol	LIMIT	Unit	
Drain-Source Voltage	V _{DS}	- 100	V	
Gate-Source Voltage	V _{GS}	± 20		
Continuous Drain Current (T _J = 150 °C) ^{a, b}	T _A = 25 °C	I _D	- 3.8	A
	T _A = 70 °C		- 2.5	
Pulsed Drain Current	I _{DM}	- 11		
Continuous Source Current (Diode Conduction) ^{a, b}	I _S	- 3.8		
Single Pulse Avalanche Current	L = 1.0 mH	I _{AS}	3.5	mJ
Single Pulse Avalanche Energy		E _{AS}	13	
Maximum Power Dissipation	T _C = 25 °C	P _D	2.7	W
	T _C = 70 °C		1.7	
	T _A = 25 °C		1.55	
	T _A = 70 °C		0.93	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	t ≤ 5 s	R _{thJA}	65	80.5	°C/W
Maximum Junction-to-Case	Steady State	R _{thJC}	30	45	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. Pulse width limited by maximum junction temperature.

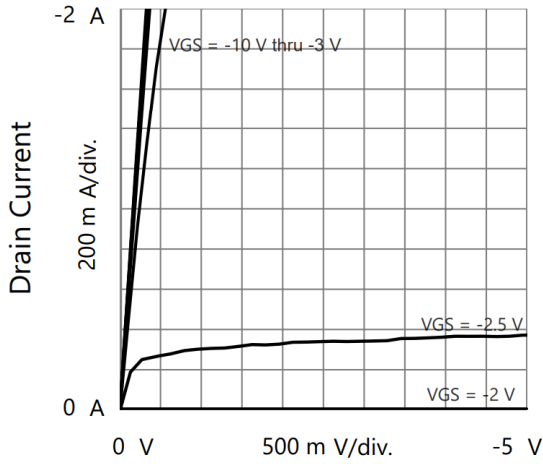
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min .	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	- 100			V
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	- 1.2		- 2.5	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -100\text{ V}, V_{GS} = 0\text{ V}$			- 1	μA
		$V_{DS} = -80\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			- 10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq -15\text{ V}, V_{GS} = -10\text{ V}$	- 3.8			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -0.5\text{ A}$		185	240	m Ω
		$V_{GS} = -4.5\text{ V}, I_D = -0.5\text{ A}$		212	290	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -25\text{ V}, I_D = -0.5\text{ A}$		2.2		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = -25\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		1250		pF
Output Capacitance	C_{oss}			50		
Reverse Transfer Capacitance	C_{rss}			34		
Total Gate Charge	Q_g	$V_{DS} = -50\text{ V}, V_{GS} = -10\text{ V}, I_D = -0.5\text{ A}$		7.9		nC
Gate-Source Charge	Q_{gs}			1.6		
Gate-Drain Charge	Q_{gd}			2.5		
Gate Resistance	R_g	$f = 1\text{ MHz}$		10		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -50\text{ V}, I_D = -0.5\text{ A},$ $V_{GEN} = -10\text{ V}, R_g = 6\text{ }\Omega$		8		ns
Rise Time	t_r			11		
Turn-Off Delay Time	$t_{d(off)}$			16		
Fall Time	t_f			11		
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_A = 25\text{ }^\circ\text{C}$			-3.8	A
Pulse Diode Forward Current ^a	I_{SM}				-11	
Body Diode Voltage	V_{SD}	$I_S = -1\text{ A}$			-1.2	V
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F = -0.5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		90		nC

Notes:

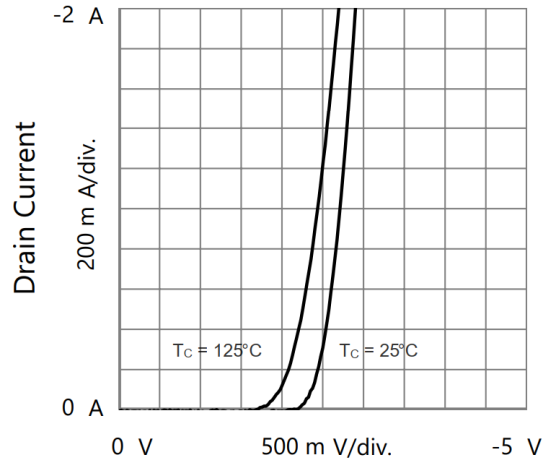
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

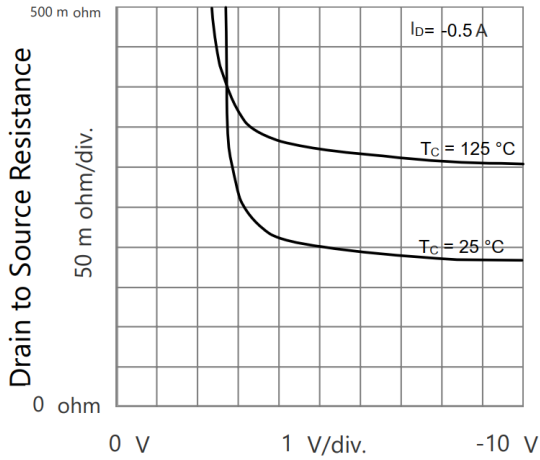
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



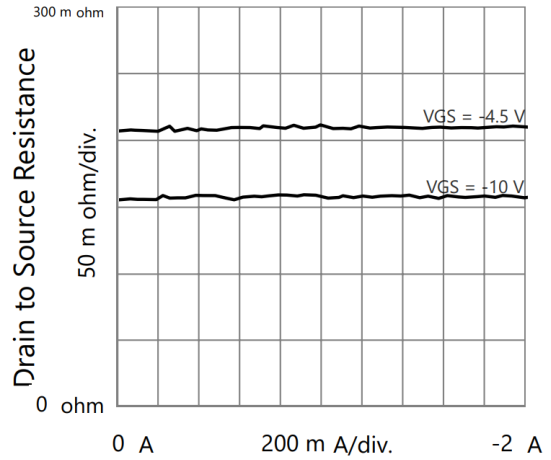
Drain to Source Voltage
Output Characteristics



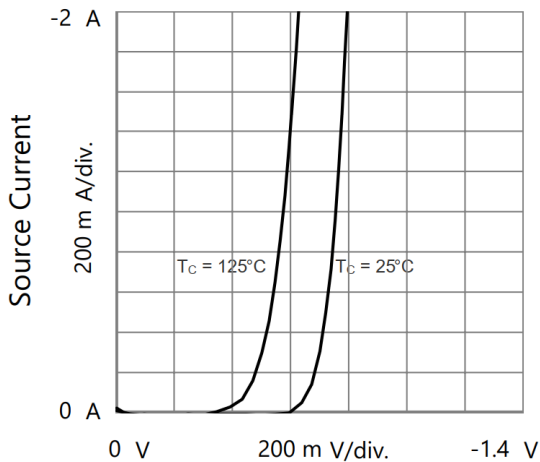
Gate to Source Voltage
Transfer Characteristics



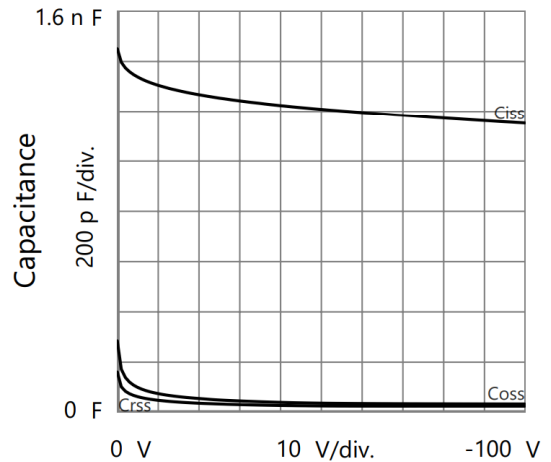
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage



Drain Current
Drain to Source Resistance vs. Drain Current

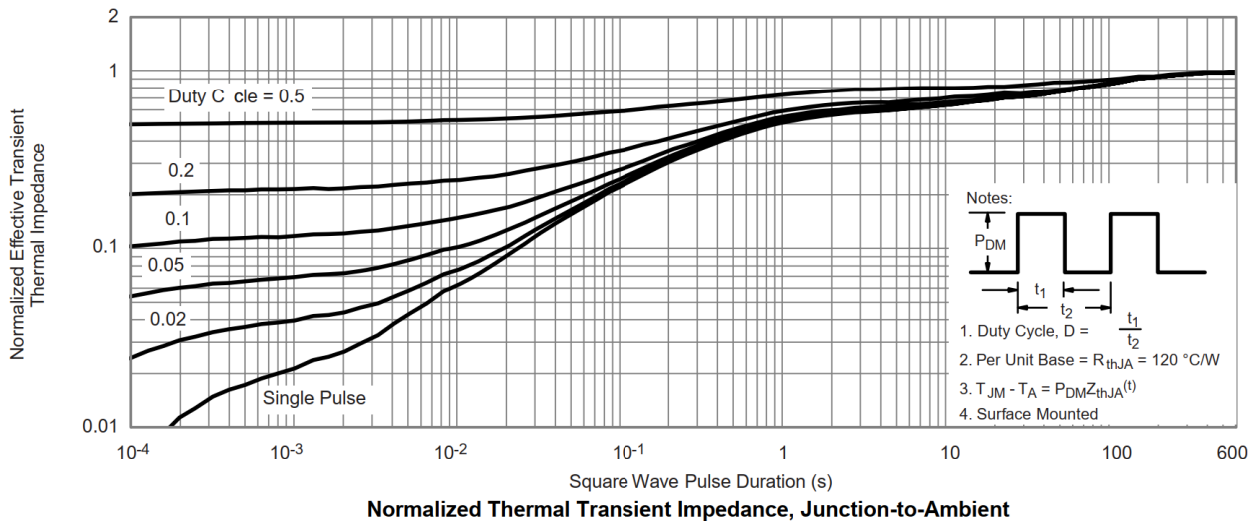
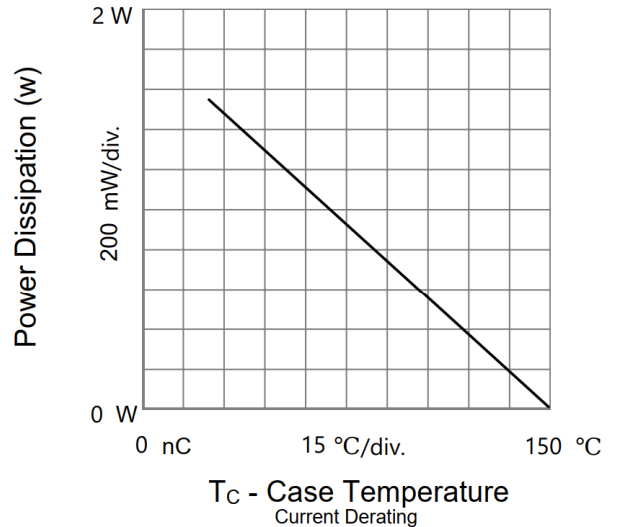
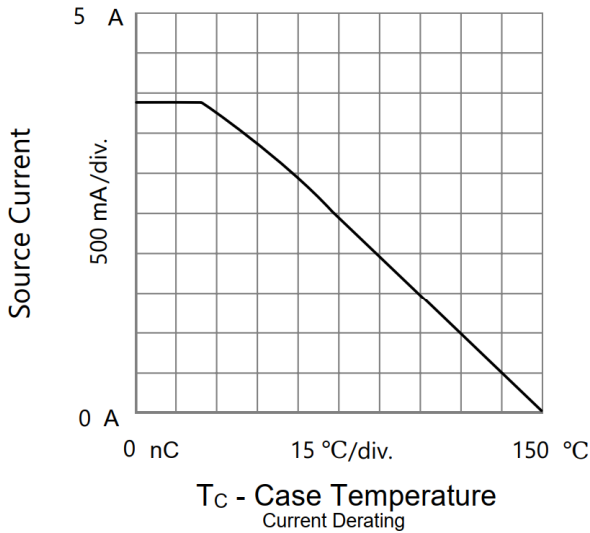
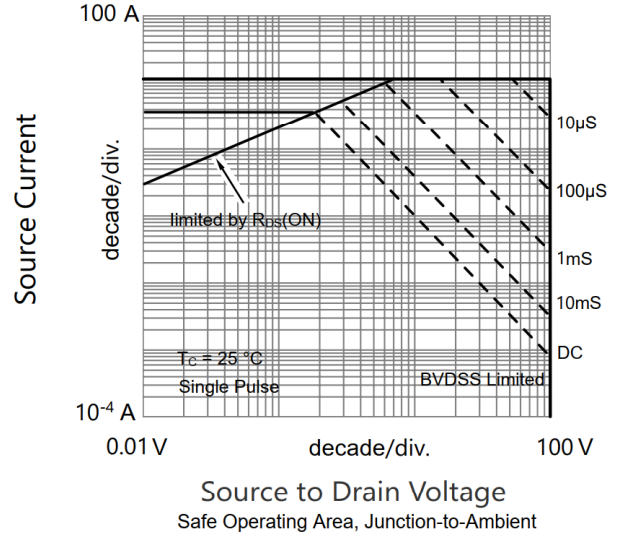
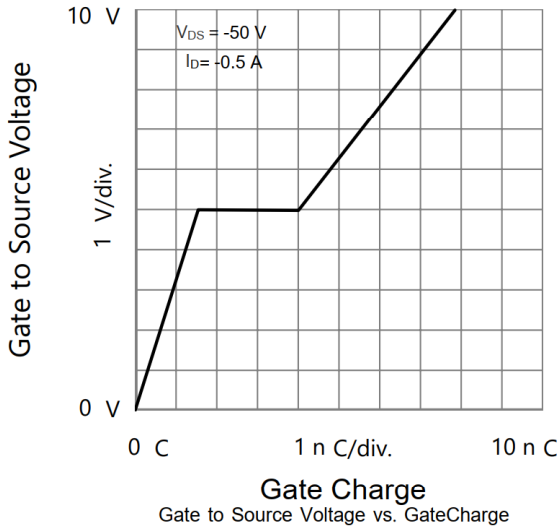


Source to Drain Voltage
Body Diode Forward Characteristics

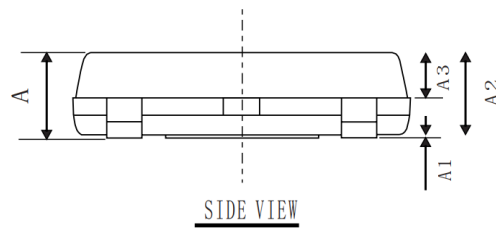
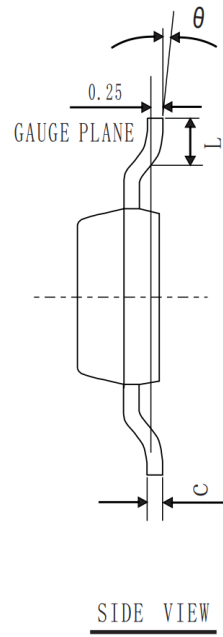
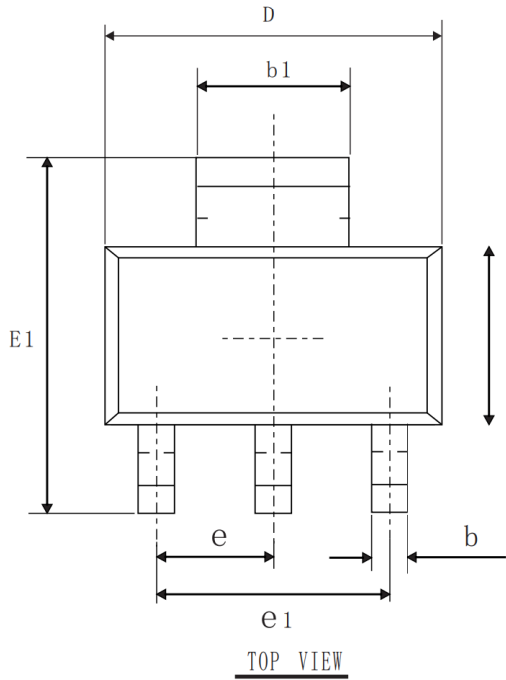


Drain to Source Voltage
Capacitances

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



SOT-223-3L PACKAGE OUTLINE



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX
A	-	-	1.95
A1	0.00	0.05	0.16
A2	1.35	1.60	1.85
A3	0.65	0.90	1.15
b	0.55	0.70	0.90
b1	2.75	3.00	3.30
C	0.18	0.30	0.42
D	6.00	6.50	7.00
E	3.10	3.50	3.90
E1	6.50	7.00	7.50
e1	4.20	4.60	5.00
L	0.78	-	1.28
θ	0°	5°	10°
e	2.3BSC		

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